

Features

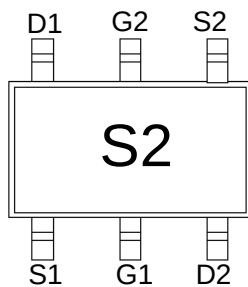
- Trench Power LV MOSFET technology
- High Power and current handing capability

Application

- PWM application
- Load switch

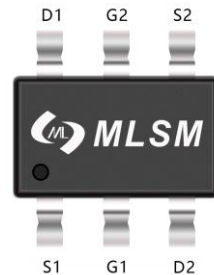
Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
20V	50mΩ@4.5V	2.5A
	69mΩ@2.5V	

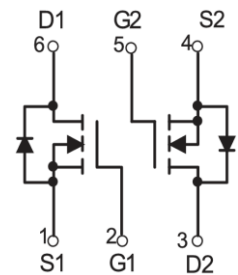


Marking and pin assignment

S2 : Device code



SOT-363 top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	20	V
V_{GS}	Gate-Source Voltage	±10	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}C$ 2.5	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$ 8	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$ 2.5	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}C$ 0.5	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	178	°C/ W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS2302DW	SOT-363	S2	3,000	45,000	180,000	7"reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.45	0.7	1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =2.5A	--	50	65	mΩ
		V _{GS} =2.5V, I _D =2.0A	--	69	85	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	200	--	pF
C _{OSS}	Output Capacitance		--	35	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	28	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =2A, V _{GS} =4.5V	--	3	--	nC
Q _{gs}	Gate Source Charge		--	0.5	--	nC
Q _{gd}	Gate Drain Charge		--	0.7	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, I _D =2A, V _{GS} =4.5V, R _G =3Ω	--	3	--	nS
t _r	Turn-on Rise Time		--	11	--	nS
t _{d(off)}	Turn-Off Delay Time		--	20	--	nS
t _f	Turn-Off Fall Time		--	8	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =2.5A	--	--	1.2	V

Typical Operating Characteristics

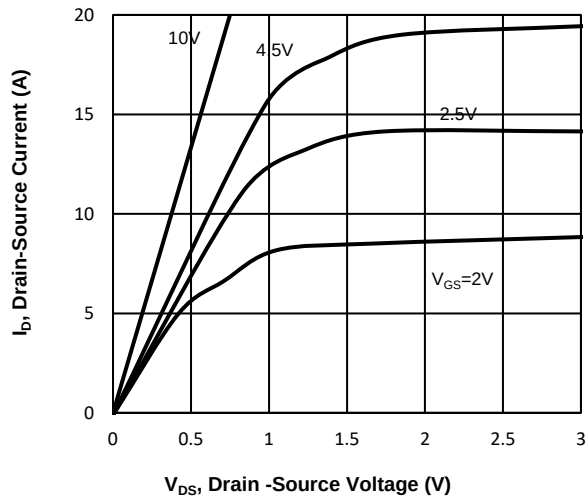


Fig1. Typical Output Characteristics

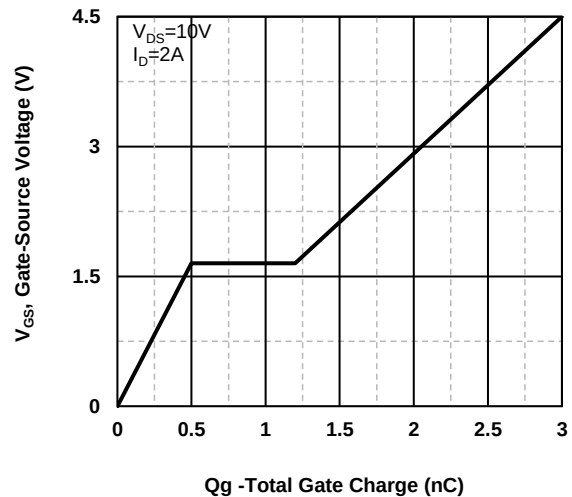


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

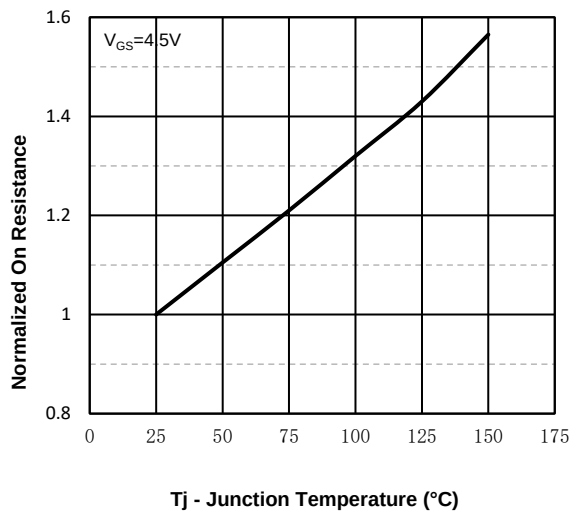


Fig3. Normalized On-Resistance Vs. Temperature

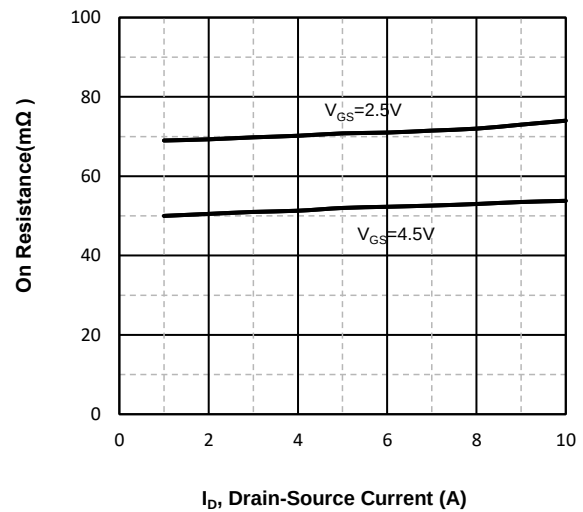


Fig4. On-Resistance Vs. Drain-Source Current

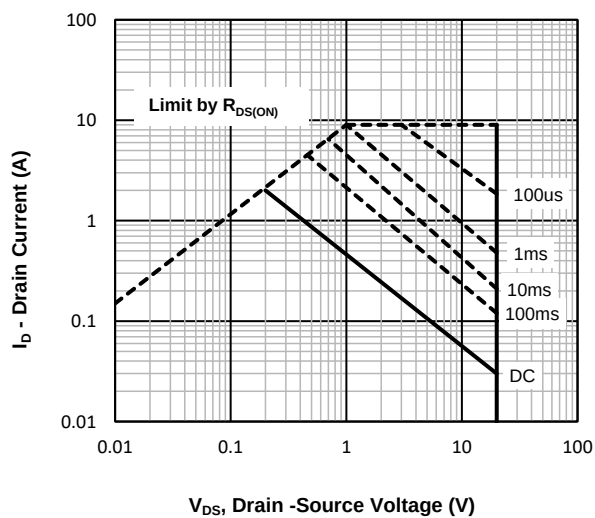


Fig5. Maximum Safe Operating Area

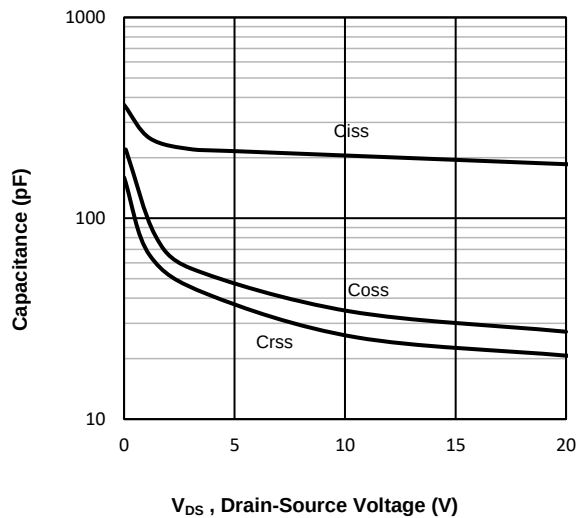
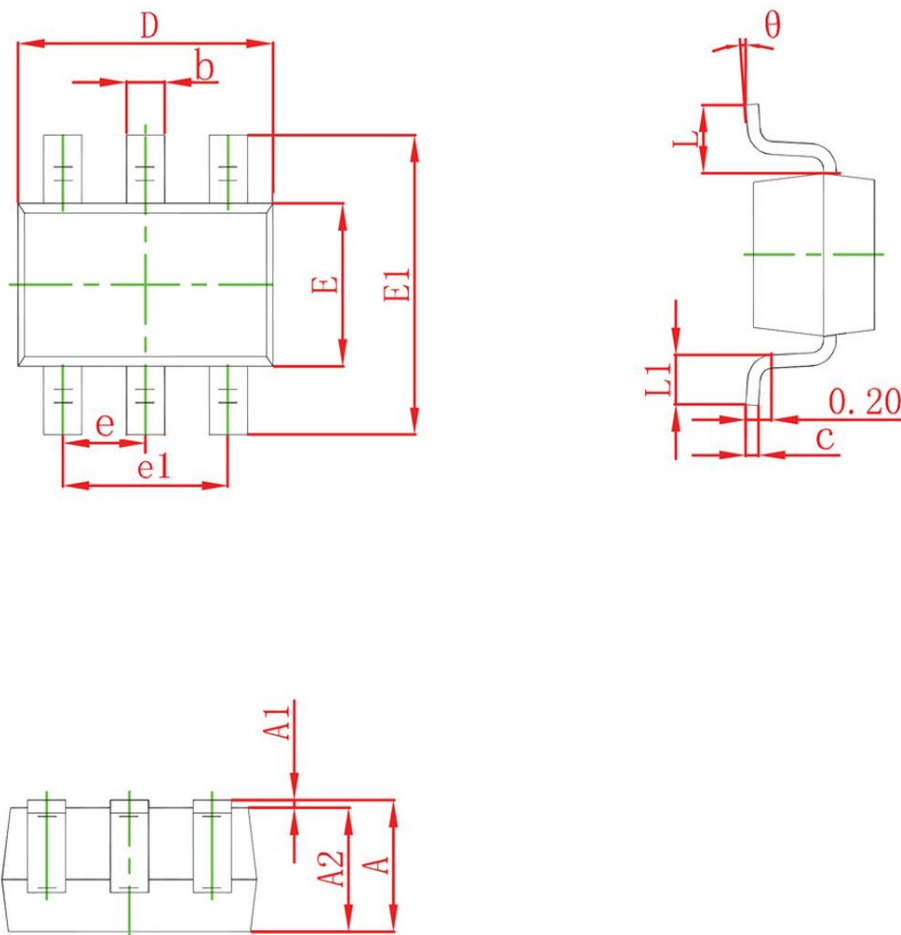


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-363 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°